

ABSTRACT OF THE DISCLOSURE

A thin film transistor substrate includes a transparent insulating substrate, a first thin film transistor that is formed on the transparent insulating substrate, and a second thin film transistor that is formed on the transparent insulating substrate. The second thin film transistor has a characteristic that differs from that of the first thin film transistor. An active layer of the first thin film transistor has a thickness greater than or equal to 50 nm, and an average crystal grain diameter greater than or equal to 1 μ m. An active layer of the second thin film transistor has a thickness less than or equal to 60 nm, and an average crystal grain diameter less than 1 μ m. The thin film transistor substrate is formed by conducting poly-crystallization through CW laser irradiation while controlling off time leak current generation and pressure resistance degradation.